Kondo E ect in a Quantum Antidot

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A bstract

W e report K ondo-like behaviour in a quantum antidot (a submicron depleted region in a two-dimensional electron gas) in the quantum H all regime. W hen both spin branches of the lowest Landau level encircle the antidot in a magnetic eld (1 T), extra resonances occur between extended edge states via antidot bound states when tunnelling is C oulom b blockaded. These resonances appear only in alternating C oulom b-blockaded regions, and become suppressed when the tem perature or source-drain bias is raised. A lthough the exact m echanism is unknown, we believe that K ondo-like correlated tunnelling arises from skyrm ion-type edge reconstruction. This observation dem onstrates the generality of the K ondo phenom enon.

O ne of the most well-studied many-body phenomena, the K ondo e ect, arises when an isolated electronic spin is present in a sea of free electrons. A reason why the K ondo e ect has attracted so much attention is that the same theoretical treatment can describe many di erent systems, such as metals containing magnetic in purities [1,2], weakly conned quantum dots $[3{5}]$, or even more exotic system swhere the role of spin is replaced by another internal degree of freedom [6]. Q uantum dots minic magnetic in purities by electrostatic connement of electrons, and the exibility in tuning various parameters has recently enabled the study of K ondo phenomena in great detail $[7{10}]$. Here, we report K ondo-like correlated tunnelling in a very di erent system, a quantum antidot $[11{14}]$, where electrons are conned magnetically (by the Lorentz force) around a submicron depleted region (antidot) in a twodimensional electron gas (2D EG). Certain features of our results, such as the absence of spin splitting of the zero-bias anomaly, imply that the system cannot be described by the conventional K ondo models. W e suggest that a skyrm ion-type edge reconstruction around the antidot leads to an enhancement of correlated tunnelling between extended edge states via the antidot.

An impurity in a metal (or a quantum dot coupled to reservoirs) is magnetic if it contains an unpaired electronic spin. At low temperature, the second- and higher-order impurity scattering processes involving spin- ip of the localised state (Fig. 1A) is enhanced if the coupling between the localised and delocalised electrons are antiferrom agnetic. This is the K ondo e ect. As a result, in the metal, the resistivity increases as it is cooled down, the opposite of ordinary metallic behaviour. In a quantum dot, the transmission between reservoirs becomes enhanced. Such a K ondo resonance occurs when the dot has an unpaired spin (i.e. when the number of electrons N in the quantum dot is odd). N can be changed by, for example, varying the voltage on a gate nearby. The conductance curve as a function of gate voltage shows pairing of resonances at low temperature, as the K ondo e ect increases the conductance of alternating C oulom b-blockaded regions and brings the two peaks close together (see the top-right diagram in Fig. 1A). This is often called odd-even behaviour.

Now, in terms of device structure, a quantum antidot (Fig. 1B) is quite di erent from a quantum dot. A magnetic eld B applied perpendicular to the plane of the 2DEG quantises the kinetic energy of the electrons into Landau levels at $(n + 1=2)h!_{c}$, where n (0) is an integer, h = h=2 (h: P lanck's constant), and $!_{c}$ is the cyclotron frequency. A long the bulk 2DEG boundaries, the Landau levels rise in energy with the electrostatic potential, and extended edge states form where the Landau levels intersect the Fermi energy. A round the antidot, electrons form localised states, travelling phase-coherently in closed orbits. Due to the Aharonov-Bohm e ect, each state encompasses an integer number of magnetic ux quanta $_{0}$ = h=e. Therefore, the average area S_i enclosed by the ith state is quantised as $BS_i = i_0$. The states are led up to the Fermi energy (led circles in Fig. 1B) and those above are empty (open circles). When B increases, each state shrinks in area (in order to keep B S_i constant), moving towards the centre of the antidot, and accumulating a net negative charge. Because the states are all quantised, the net charge cannot relax until enough charge (e=2) has built up, at which point an electron leaves and the net charge jumps to e=2 [13]; the process then repeats with period B = h=eS, where S is the area enclosed by a state at the Fermi energy. This periodic depopulation can be observed in conductance measurements if the current-carrying extended edge states are brought close to the antidot so that electrons tunnel between them (see Fig. 1B). Here, the conductance decreases on resonance, because the resonance enhances backscattering (between opposite edges). This resonance process when sweeping B resembles that when sweeping gate voltage in quantum dots: o resonance, tunnelling is Coulom b blockaded due to the discreteness of the electronic charge.

Samples were fabricated from a GaAs/A GaAs quantum -well structure containing a 2DEG situated 300 nm below the surface with a sheet density 3 10^{15} m² and mobility 500 m²/Vs. On top of the substrate, m etal Schottky gates (10 nm N iC r/30 nm Au) were patterned by electron-beam lithography (top-right inset of Fig. 1B). A second m etal layer (30 nm N iC r/70 nm Au) was patterned on top of 350 nm cross-linked polym ethylm ethacry-late (PM M A) [15] in order to contact the central dot gate so that voltages can be applied to the three gates independently. A negative voltage on the dot gate, 0.3 m on a side, creates an antidot by depleting electrons undemeath. The depleted region can be approximated to be circular, with a radius of 0.36 0.40 m, depending on the voltage used; the radius is deduced from the Aharonov-Bohm period B. The two side gates, which are used to bring the extended edge states close to the antidot, form parallel one-dimensional constrictions, each with lithographic width 0.7 m and length 0.3 m. The measurem ents were performed in a dilution refrigerator with a base temperature 25 m K.

The conductance measurements were performed as follows. A 5 VAC excitation voltage at 77 Hz was applied between the ohm ic contacts 1 and 3 shown in the bottom-left inset to Fig. 2 and the current I was measured using a lock-in amplier. Simultaneously, the diagonal voltage drop V_{dg} between the contacts 2 and 4 was measured, and the antidot conductance was calculated as $G_{ad} = I = V_{dg}$. In the quantum Hall regime (with the correct direction of edge current ow), this four-term inal measurement gives the 'true' [16] two-term inal conductance $G_{ad} = _ce^2 = h$, where $_c$ is the number of led Landau levels in the antidot constrictions [17]. The lling factors in the constrictions and the coupling between the extended edge states and the antidot states can be tuned by the voltages on the side gates, and they were kept as symmetric as possible throughout the measurements.

The number of Landau levels forming bound states around the antidot is de ned by the number of edge states transmitted through the constrictions. Figure 2 shows a typical G_{ad} vs B curve taken at 25 m K when the two spins of the lowest Landau level encircle the antidot; c decreases from 2 to 1 as B increases. At low B where G_{ad} is close to the c = 2 quantum – H all plateau value $2e^2$ =h, a series of pairs of dips (two dips per B) can be seen. As B increases, and as the coupling between the leads and the antidot becomes stronger (because the edge states move towards the centre of the constrictions), the amplitude of the dips increases. A loo, the gaps inside pairs (intra-pair gaps) seem to be led up, and eventually the pairs become e unrecognisable as two independent dips above 1.3 T as G_{ad} approaches the c = 2 and 1 plateaux with di erent gate-voltage settings and with di erent B ranging from 0.8 to 1.5 T in m any samples and on m any therm al cycles. At higher m agnetic elds (> 3 T), the pairing of the resonances disappears, but instead the oscillations become e pure double-frequency [11,14].

These pairsm ay simply seem to be spin-split pairs (each dip corresponding to a resonance of either spin). The di erence in the amplitude of alternating dips may be an indication of di erent coupling strength for each spin. However, curve tting (top-right diagram in Fig. 2) shows that the feature in the intra-pair gap cannot be explained by such a simplistic model [18]. Strikingly, the paired resonances in Fig. 2, if shown upside down, look very sim ilar to C oulom b-blockade oscillations with K ondo resonances in quantum dots (top-right diagram in Fig. 1A). We argue that the discrepancy in the intra-pair gaps is caused by K ondo resonances, based on the results from the nonequilibrium and temperature activation m easurem ents described below.

The behaviour of K ondo resonances under nonequilibrium conditions has been well studied in quantum dots [7{10]. Under a nite source-drain bias, m ism atch in the chem ical potentials of the source and drain suppresses the K ondo resonance. In our experiments, when a small source-drain D C bias V_{sd} is applied in addition to the AC excitation, the K ondo feature' lling each intra-pair gap vanishes, having two well-de ned dips as shown in Fig. 3A. The K ondo features appear as horizontal red/dark lines (zero-bias anom aly) around $V_{sd} = 0$ when G_{ad} is plotted in colour-scale against V_{sd} and B (Fig. 3B). Note that here the horizon-tal axis is B instead of V_g , as is norm ally the case for quantum dots. The zero-bias anom aly becomes stronger as B, and hence the coupling, increase. The diam ond-shaped structures of red lines arise because each resonance splits into two under a nite bias due to the di erence in the chem ical potentials of the two leads. From the height of each diam ond, the energy to add an extra electron (charging energy) can be estimated to be 60 eV. W hen the coupling is made even stronger, the zero-bias anom aly is still clearly visible, whereas the diam ond structures are sm eared out due to weak con nem ent (Fig. 3C).

Increasing tem perature T suppresses our K ondo feature, leaving the intra-pair gaps better de ned (Fig. 3D and E). At around 190 mK, the intra-pair and inter-pair gaps become alm ost indistinguishable. At lower B where intra-pair gaps are alm ost as well de ned as inter-pair gaps, increasing T broadens each dip, and the conductance in both gaps decreases (as expected w ithout the K ondo e ect). However, at higher B, the conductance in the intra-pair gaps increases. Because the feature disappears into the noise level at relatively low T, it was not possible to study the tem perature dependence in m ore detail, e.g. to determ ine the K ondo tem perature T_K , which norm ally m arks the crossover between logarithm ic (high

T) and power-law (low T) behaviours. We note that the amplitude of our K ondo feature decreases m onotonically as T increases.

The above behaviour of the antidot conductance is qualitatively very similar to that of K ondo resonances in a quantum dot. It appears that as the antidot states are depopulated one by one when B is increased, a localised m agnetic m on entarises when there is an unpaired electronic spin. Then, when the coupling between the extended and antidot edge states is strong, K ondo resonances enhance the tunnelling through the antidot in the C oulom b-blockaded region. Stronger coupling results in larger T_K , and hence the zero-bias anom aly is m ore pronounced in the region closer to the $_c = 1$ plateau (where the wavefunctions of the extended and antidot states strongly overlap).

However, there is a crucial di erence in our results from those in quantum dots. In a quantum dot in a comparable magnetic eld, the Zeem an energy $E_z = jgj_BB$ ($_B$ is Bohrm agneton and g = 0.44 in bulk G aA s) usually splits the zero-bias anomaly into two parallel lines separated by $2E_z = e$. The K ondo resonance is suppressed at $V_{sd} = 0$ because spin degeneracy is lifted [7,8,10]. At B = 1.2 T, $E_z = 30$ eV, but the width of our zero-bias anomaly is 20 V. Thus, the energy gap between the opposite spin states must be at most 10 eV, and probably much smaller. This is at least a factor of 3 less than E_z .

O ne possible explanation for this lack of spin-splitting is to consider an accidental degeneracy between neighbouring orbital states with opposite spins. This might occur if E_z happened to be close to an integer multiple of the single-particle energy spacing E_{sp} (the di erence in potential energy between neighbouring states; see Fig. 1C). However, since $E_{sp} / 1=B$ if a constant potential is assumed, the ratio $E_z = E_{sp} / B^2$ would not stay constant over a wide range of B. As we have observed the e ect under many di erent conditions, it is highly unlikely that this accidental degeneracy is the cause.

Another important issue in our experiments is that the conductance dips saturate at $e^2 = h$ (Fig.2), forming the $_c = 1$ plateau as B increases and the oscillations die away. The existence of the $_c = 1$ plateau implies that the extended edge states of the lower spin state are perfectly transmitted through the constructions, and not coupled to the antidot. This causes another di culty in the interpretation, because, for ordinary K ondo resonances to occur, both spins in the leads need to be coupled to the localised state.

It is likely that the edge-state picture shown so far needs to be modiled to a many-body picture. Recently, we have demonstrated that a self-consistent treatment of the antidot potential is in portant, especially at higher B [14]. Taking into account the form ation of two concentric compressible rings (where states are partially led, and are pinned at the Ferm i energy; see Fig. 1D) [19], we have successfully explained double-frequency A haronov-B ohm oscillations observed at higher B [11]. However, this is not yet enough for the K ondo e ect, as either only one spin (outer ring) would be coupled to the leads, or, if both spins were coupled to the leads, there would be no $_{c} = 1$ plateau.

It has been shown that in a relatively weak magnetic eld, an excited state of a = 1 quantum Hall liquid is not simply a spin ip, but rather, a complicated spin texture, called a skyrm ion [20], which form sdue to strong correlations. Recent work has shown that skyrm ion-type edge reconstruction is important in quantum dots in the quantum Hall regim e [21,22]. If we assume that such correlated states form in the regions of the antidot and extended edge states where the local lling factor is 1 < < 2 (Fig. 1E), electrons with both spins there would be allowed to tunnel, whether the local ledge states are coupled or not. The excitation

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energy of correlated states is typically smaller than E_z . If two con gurations, in which the total spin di ers by one, are (alm ost) degenerate, this may allow spin- ip tunnelling. It is uncertain, how ever, whether the odd-even behaviour can occur with such strongly correlated states.

In sum mary, we have shown that an antidot in the quantum Hall regime qualitatively exhibits all the features of the K ondo e ect, despite the lack of an obvious reason for spin degeneracy. We have suggested possible ways in which the edge-state picture may be modi ed to take account of interactions. The fact that the antidot is an open system further complicates the problem, in comparison with quantum dots, where only a limited num – ber of states are considered. A detailed theoretical calculation is needed to determ ine the edge-state structure that gives rise to the K ondo-like behaviour in an antidot.

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R eferences and N otes

- [1] J.Kondo, Prog. Theor. Phys. 32, 37 (1964).
- [2] For a review, see A.C. Hew son, The K ondo P roblem to Heavy Ferm ions (C am bridge U niversity P ress, C am bridge, 1993).
- [3] L.I.G lazm an and M.E.Raikh, JETP Lett. 47, 452 (1988).
- [4] T.K.Ng and P.A.Lee, Phys.Rev.Lett. 61, 1768 (1988).
- [5] Y.Meir, N.S.W ingreen, and P.A.Lee, Phys. Rev. Lett. 70, 2601 (1993).
- [6] D.L.Cox and A.Zawadowski, Advances in Physics 47, 599 (1998).
- [7] D. Goldhaber-Gordon, H. Shtrikman, D. Mahalu, D. Abusch-Magder, U. Meirav, and M.A.Kastner, Nature 391, 156 (1998).
- [8] S.M. Cronenwett, T.H. Oosterkamp, and L.P.Kouwenhoven, Science 281, 540 (1998).
- [9] W. G. van der Wiel, S. De Franceschi, T. Fujisawa, J. M. Elzerman, S. Tarucha, and L.P. Kouwenhoven, Science 289, 2105 (2000).
- [10] M.Keller, U.W ilhelm, J.Schmid, J.Weis, K.von Klitzing, and K.Eberl, Phys. Rev. B 64, 033302 (2001).
- [11] C.J.B.Ford, P.J.Simpson, I.Zailer, D.R.Mace, M.Yosen, M.Pepper, D.A.Ritchie, J.E.F.Frost, M.P.Grim shaw, and G.A.C.Jones, Phys. Rev. B 49, 17456 (1994).
- [12] V.J.Goldm an and B.Su, Science 267, 1010 (1995).
- [13] M.Kataoka, C.J.B.Ford, G.Faini, D.Mailly, M.Y.Simmons, D.R.Mace, C.-T.Liang, and D.A.Ritchie, Phys. Rev. Lett. 83, 160 (1999).
- [14] M.Kataoka, C.J.B.Ford, G.Faini, D.Mailly, M.Y.Simmons, and D.A.Ritchie, Phys.Rev. B 62, R4817 (2000).
- [15] I. Zailer, J. E. F. Frost, V. Chabasseur-Molyneux, C. J. B. Ford, and M. Pepper, Sem icond. Sci. Technol. 11, 1235 (1996).
- [16] True' in the sense that the two-term inal conductance is not a ected by the series resistance of the experim ental circuit.
- [17] M. Buttiker, Phys. Rev. Lett. 57, 1761 (1986).

- [18] In Ref. 14, we gave a model with transmission and rejection resonances in an attempt to explain similar oscillations, however this model does not explain the temperature and sourcedrain bias measurements shown here.
- [19] D.B.Chklovskii, B.I.Shklovskii, and L.I.G lazman, Phys. Rev. B 46, 4026 (1992).
- [20] S.L. Sondhi, A. Karlhede, S.A. Kivelson, and E. H. Rezayi, Phys. Rev. B 47, 16419 (1993).
- [21] P. Hawrylak, C. Gould, A. Sachrajda, Y. Feng, Z. Wasilewski, Phys. Rev. B 59, 2801 (1999).
- [22] C. Tejedor and L. Martin-Moreno, Phys. Rev. B 63, 35319 (2001).

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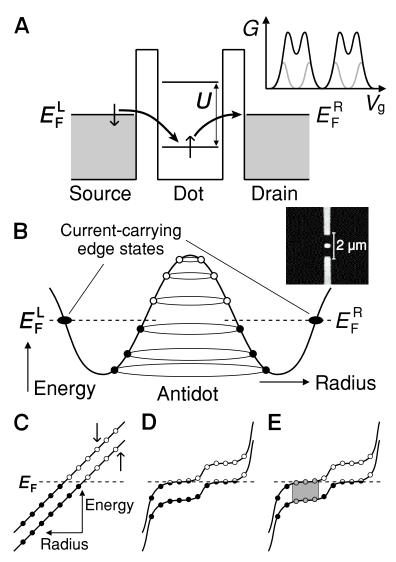


FIG.1. (A) Spin- ip tunnelling through a Coulom b-blockaded quantum dot (U: charging energy). The K ondo e ect enhances higher-order processes of such tunnelling at low tem perature. The top-right diagram shows the conductance G of the dot versus gate voltage V_g with (black) and without (grey) K ondo resonances. (B) A Landau level near the antidot and constrictions. The circular orbits of lled and empty states are represented by lled and open circles, respectively. Filled ovals represent the extended edge states, which determ ine the current through the sam ple. Top-right inset: a scanning electron m icrograph of a device prior to the second-layer m etallisation. (C) A Landau level near the Ferm i energy around the antidot with an accidental spin degeneracy between neighbouring states. (D) Self-consistent potential with two com pressible regions (one for each spin). (E) As D but with correlated states (shadowed in grey) in the 1 < < 2 region.

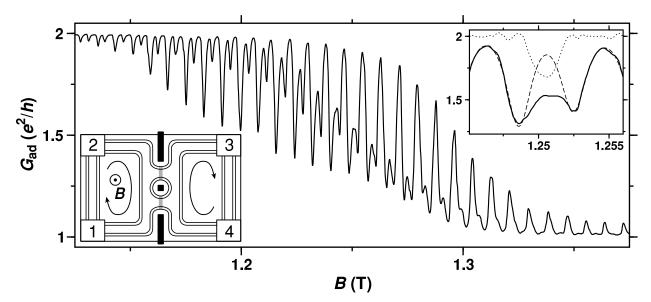


FIG.2. A typical antidot conductance G_{ad} vs B curve at 25 mK between the $_c = 2$ and 1 plateaux. The pairs of dips in ply backscattering resonances through alternating spin states. However, detailed study of the oscillations indicates that K ondo resonances occur inside the pairs. Top-right inset: the results of a t conducted for the pair around B = 1.25 T by using four dips proportional to the derivative of Ferm i function. The solid line is the experim ental curve and the dashed line is the t. The two pairs for the pair can never t the curve inside the pairs). The dotted line is the difference between the experimental curve and the t (o set by $2e^2=h$). Bottom -left inset: schem atic showing the sample geometry with four edge states (solid lines), two of each spin. A rrow s indicate the direction of electron ow. G rey lines show where tunnelling occurs between the extended edge states and the antidot states. The numbered rectangles on the corners represent ohm ic contacts.

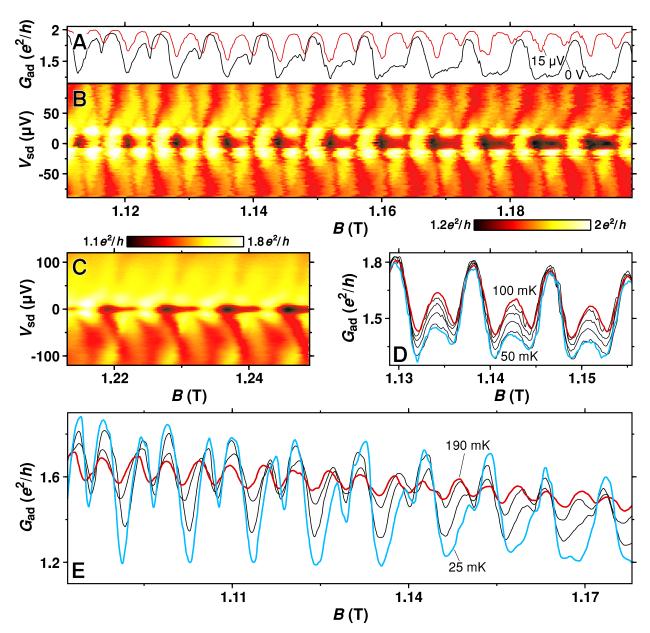


FIG.3. (A) G_{ad} vs B curves at 25 m K with source-drain bias $V_{sd} = 0$ V (black curve) and with $V_{sd} = 15$ V (red curve). The odd-even feature seen at zero bias almost disappears when a sm allbias is applied. (B) C obur-scale plot of the di erential conductance G_{ad} against B and V_{sd} . As the coupling between the leads and antidot becomes stronger (as B increases), the zero-bias anom aly becomes stronger. (C) D C-bias measurements plotted in the same manner as in B.Here, the coupling is larger, so the diam ond structure is unclear, whereas the zero-bias anom aly is clearly visible. (D) Temperature dependence of G_{ad} vs B with sm all increments of temperature (10 m K). The feature lling the gap inside each pair weakens as the temperature T is increased, leaving the gaps inside pairs better de ned at higher temperature, which is a signature of the K ondo e ect. (E) Temperature dependence of G_{ad} vs B over a wide range of T. The odd-even feature at low T (blue curve) disappears as T is raised to 190 m K (red curve), showing alm ost double-frequency oscillations.